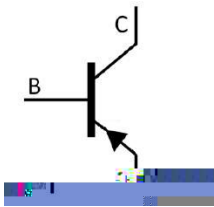
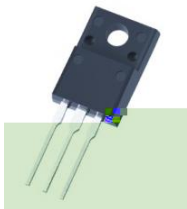


TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

Low saturation voltage, excellent dependence of h_{FE} on current, fast switching time.

Lamp drivers, power amplifiers, high-speed switching.



PIN1 Base PIN 2 Collector PIN 3 Emitter

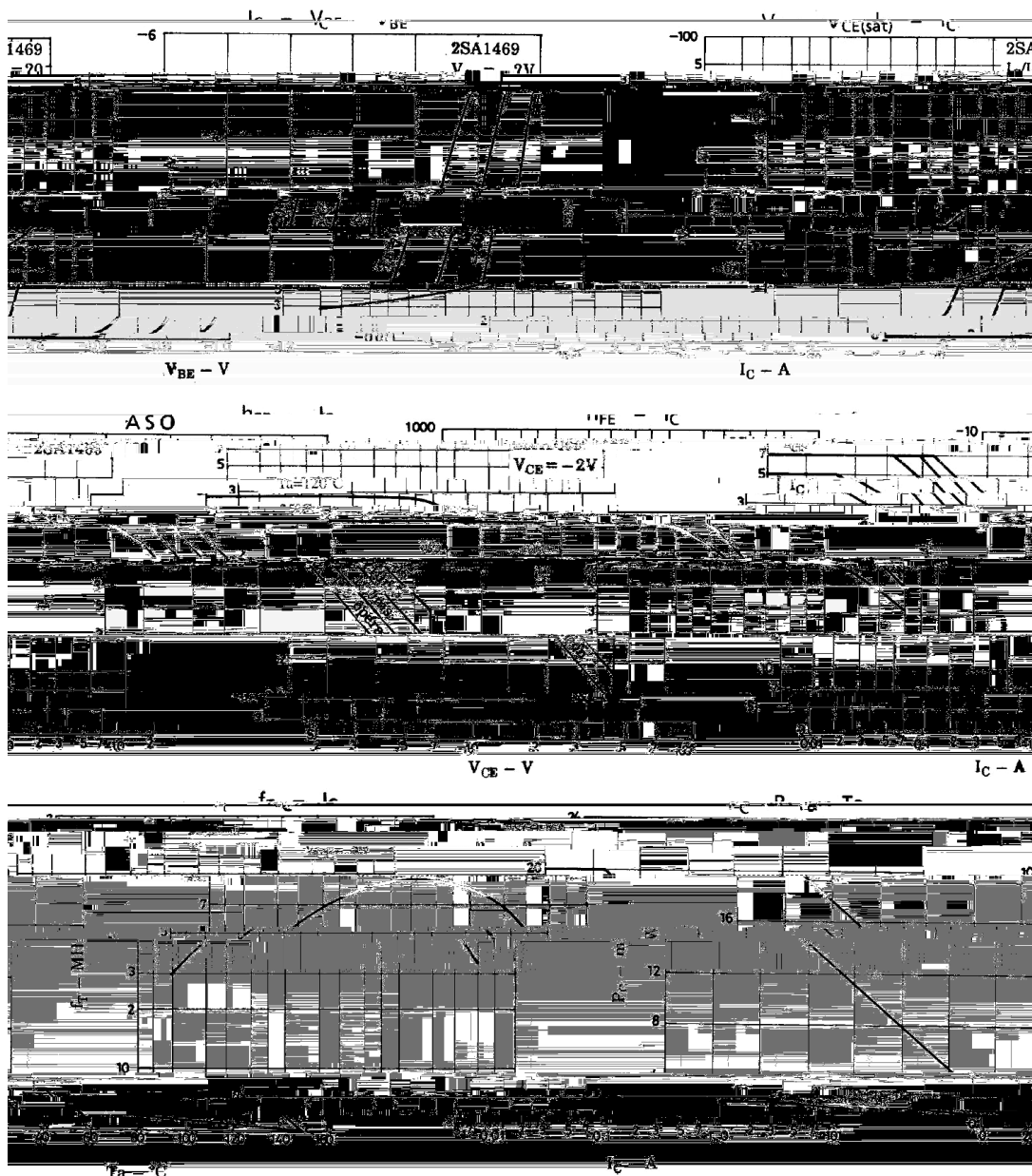
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-7.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25)$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-1.0mA$ $I_E=0$	-80			V
Collector to Base Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-1.0mA$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-40V$ $I_E=0$			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0V$ $I_C=0$			-0.1	mA
DC Current Gain	h_{FE}	$V_{CE}=-2.0V$ $I_C=-1.0A$	70		280	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2.5A$ $I_B=-0.125A$			-0.4	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_C=-1.0A$		100		MHz
Turn-On Time	t_{on}	$20I_{B1}=-20I_{B2}=I_C=2A$		0.1		s
Storage Time	t_{stg}			0.5		
Fall Time	t_f			0.1		

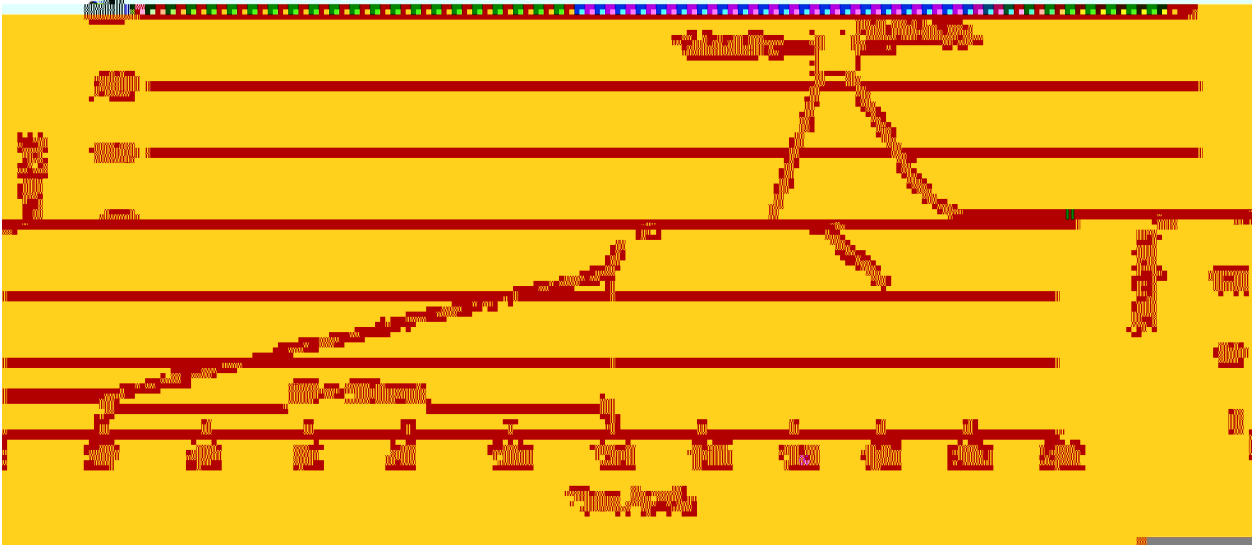
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10 /sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

5	•	⌀	B	I	255±
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